# **Power MOSFET**

# 60 V, 6.1 m $\Omega$ , 71 A, Single N-Channel

#### **Features**

- Small Footprint (5x6 mm) for Compact Design
- Low R<sub>DS(on)</sub> to Minimize Conduction Losses
- Low Q<sub>G</sub> and Capacitance to Minimize Driver Losses
- NVMFS5C670NLWF Wettable Flank Option for Enhanced Optical Inspection
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

#### MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V <sub>DSS</sub>	60	V
Gate-to-Source Voltage			$V_{GS}$	±20	V
Continuous Drain	Steady	T <sub>C</sub> = 25°C	I <sub>D</sub>	71	Α
Current R <sub>θJC</sub> (Notes 1, 3)		T <sub>C</sub> = 100°C		50	
Power Dissipation	State	T <sub>C</sub> = 25°C	P <sub>D</sub>	61	W
R <sub>θJC</sub> (Note 1)		T <sub>C</sub> = 100°C		31	
Continuous Drain		T <sub>A</sub> = 25°C	I <sub>D</sub>	17	Α
Current R <sub>0JA</sub> (Notes 1, 2, 3)	Steady	T <sub>A</sub> = 100°C		12	
Power Dissipation	State	T <sub>A</sub> = 25°C	P <sub>D</sub>	3.6	W
R <sub>θJA</sub> (Notes 1 & 2)		T <sub>A</sub> = 100°C		1.8	
Pulsed Drain Current	$T_A = 25$	°C, t <sub>p</sub> = 10 μs	I <sub>DM</sub>	440	Α
Operating Junction and Storage Temperature			T <sub>J</sub> , T <sub>stg</sub>	-55 to + 175	°C
Source Current (Body Diode)			I <sub>S</sub>	68	Α
Single Pulse Drain-to-Source Avalanche Energy (I <sub>L(pk)</sub> = 3.6 A)			E <sub>AS</sub>	166	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			TL	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case - Steady State	$R_{\theta JC}$	2.4	°C/W
Junction-to-Ambient - Steady State (Note 2)	$R_{\theta JA}$	41	

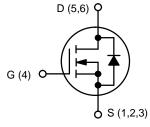
- 1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
- 2. Surface-mounted on FR4 board using a 650 mm<sup>2</sup>, 2 oz. Cu pad.
- 3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.



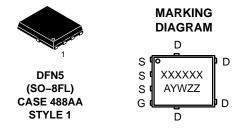
### ON Semiconductor®

#### www.onsemi.com

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> MAX	I <sub>D</sub> MAX
60 V	6.1 mΩ @ 10 V	71 A
00 V	8.8 mΩ @ 4.5 V	TIA



**N-CHANNEL MOSFET** 



XXXXXX = 5C670L

(NVMFS5C670NL) or

670LWF

(NVMFS5C670NLWF) = Assembly Location

= Year

W = Work Week

= Lot Traceability

#### ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 5 of this data sheet.

# **ELECTRICAL CHARACTERISTICS** (T<sub>J</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Тур	Max	Unit
OFF CHARACTERISTICS	•			-	-	-	-
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		60			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V <sub>(BR)DSS</sub> /				27		mV/°C
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V,	T <sub>J</sub> = 25 °C			10	^
		$V_{DS} = 60 \text{ V}$	T <sub>J</sub> = 125°C			250	μΑ
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = 20 V				100	nA
ON CHARACTERISTICS (Note 4)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	$V_{GS} = V_{DS}, I_{D} = 53 \mu A$		1.2		2.0	V
Threshold Temperature Coefficient	V <sub>GS(TH)</sub> /T <sub>J</sub>				-4.7		mV/°C
Drain-to-Source On Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 35 A		5.1	6.1	mΩ
		V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 35 A		7.0	8.8	
Forward Transconductance	9FS	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 35 A			82		S
CHARGES AND CAPACITANCES							
Input Capacitance	C <sub>ISS</sub>	V <sub>GS</sub> = 0 V, f = 1 MHz, V <sub>DS</sub> = 25 V			1400		pF
Output Capacitance	C <sub>OSS</sub>				690		
Reverse Transfer Capacitance	C <sub>RSS</sub>				15		
Total Gate Charge	Q <sub>G(TOT)</sub>	V <sub>GS</sub> = 4.5 V, V <sub>DS</sub> = 48 V; I <sub>D</sub> = 35 A			9.0		nC
Total Gate Charge	Q <sub>G(TOT)</sub>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 48 V; I <sub>D</sub> = 35 A			20		nC
Threshold Gate Charge	Q <sub>G(TH)</sub>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 48 V; I <sub>D</sub> = 35 A			2.5		nC
Gate-to-Source Charge	Q <sub>GS</sub>				4.5		
Gate-to-Drain Charge	$Q_{GD}$				2.0		
Plateau Voltage	$V_{GP}$				3.1		V
SWITCHING CHARACTERISTICS (Note	5)			•	•	•	
Turn-On Delay Time	t <sub>d(ON)</sub>	$V_{GS} = 4.5 \text{ V}, V_{DS} = 48 \text{ V},$ $I_{D} = 35 \text{ A}, R_{G} = 2.5 \Omega$			11		- ns
Rise Time	t <sub>r</sub>				60		
Turn-Off Delay Time	t <sub>d(OFF)</sub>				15		
Fall Time	t <sub>f</sub>				4		
DRAIN-SOURCE DIODE CHARACTERI	STICS				•		•
Forward Diode Voltage	V <sub>SD</sub>	$V_{GS} = 0 \text{ V},$ $I_{S} = 35 \text{ A}$	T <sub>J</sub> = 25°C		0.9	1.2	
			T <sub>J</sub> = 125°C		0.8		V
Reverse Recovery Time	t <sub>RR</sub>	$V_{GS} = 0 \text{ V, } dI_{S}/d_{t} = 100 \text{ A/}\mu\text{s,}$ $I_{S} = 35 \text{ A}$			34		
Charge Time	t <sub>a</sub>				17		ns
Discharge Time	t <sub>b</sub>				17		
Reverse Recovery Charge	Q <sub>RR</sub>				19		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: pulse width  $\leq 300~\mu s$ , duty cycle  $\leq 2\%$ .

5. Switching characteristics are independent of operating junction temperatures.

#### TYPICAL CHARACTERISTICS

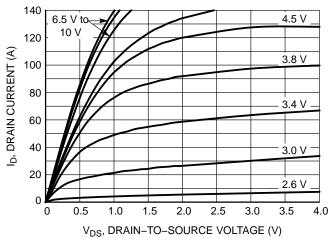


Figure 1. On-Region Characteristics

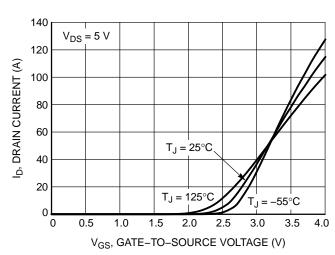


Figure 2. Transfer Characteristics

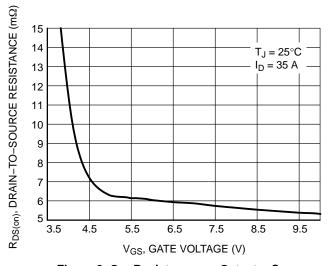


Figure 3. On-Resistance vs. Gate-to-Source Voltage

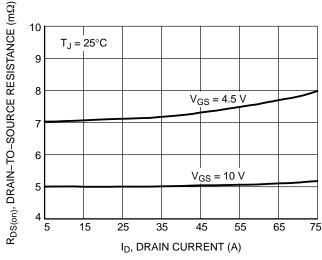


Figure 4. On–Resistance vs. Drain Current and Gate Voltage

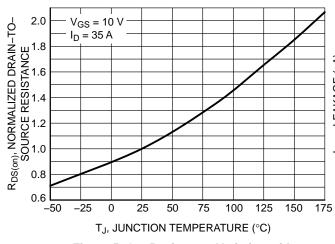


Figure 5. On–Resistance Variation with Temperature

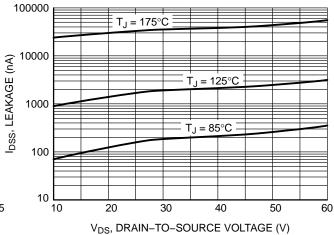


Figure 6. Drain-to-Source Leakage Current vs. Voltage

#### TYPICAL CHARACTERISTICS

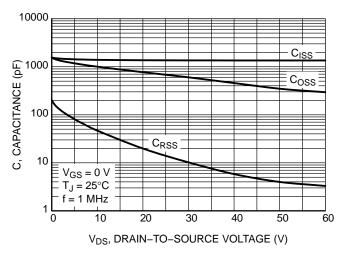


Figure 7. Capacitance Variation

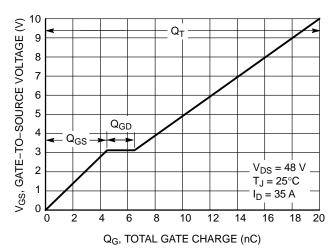


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

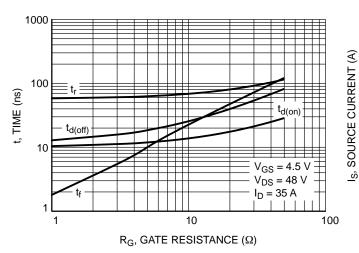


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

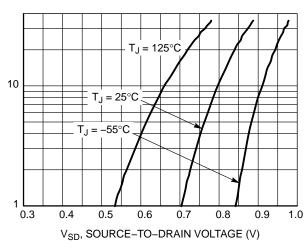


Figure 10. Diode Forward Voltage vs. Current

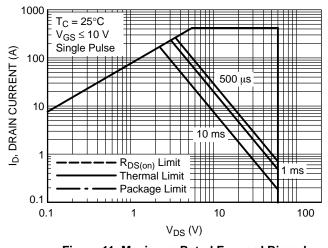


Figure 11. Maximum Rated Forward Biased Safe Operating Area

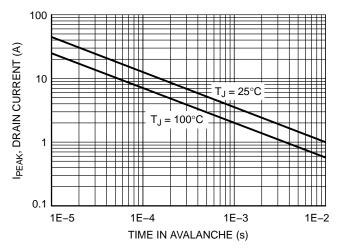


Figure 12. Maximum Drain Current vs. Time in Avalanche

# **TYPICAL CHARACTERISTICS**

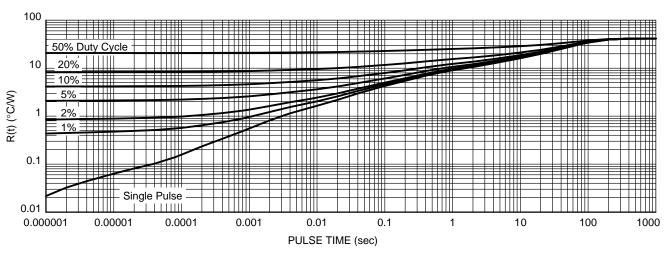


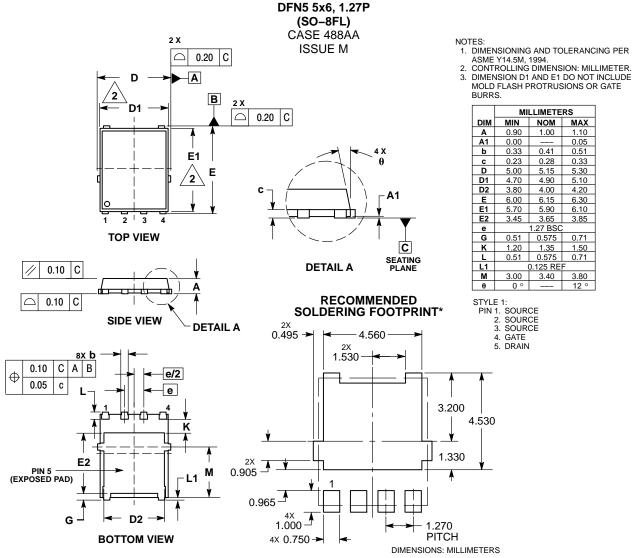
Figure 13. Thermal Characteristics

#### **DEVICE ORDERING INFORMATION**

Device	Marking	Package	Shipping <sup>†</sup>
NVMFS5C670NLT1G	5C670L	DFN5 (Pb-Free)	1500 / Tape & Reel
NVMFS5C670NLWFT1G	670LWF	DFN5 (Pb-Free, Wettable Flanks)	1500 / Tape & Reel
NVMFS5C670NLT3G	5C670L	DFN5 (Pb-Free)	5000 / Tape & Reel
NVMFS5C670NLWFT3G	670LWF	DFN5 (Pb–Free, Wettable Flanks)	5000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### PACKAGE DIMENSIONS



\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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